Transport and structural study of pressure induced m agnetic states in N d_{0:55} Sr_{0:45}M nO _3 and N d_{0:5} Sr_{0:5}M nO _3

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P ressure e ects on the electron transport and structure of N d_{1 x} Sr_x M nO₃ (x = 0.45, 0.5) were investigated in the range from ambient to 6 G Pa. In N d_{0.55} Sr_{0.45} M nO₃, the low temperature ferrom agnetic metallic state is suppressed and a low temperature insulating state is induced by pressure. In N d_{0.55} Sr_{0.5}M nO₃, the CE -type antiferrom agnetic charge-ordering state is suppressed by pressure. Under pressure, both samples have a similar electron transport behavior although their ambient ground states are much di erent. It is sum ised that pressure induces an A-type antiferrom agnetic state at low temperature in both compounds.

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In Nd_{1 x}Sr_xM nO₃ m anganite, the size di erence between Nd³⁺ and Sr²⁺ is large (0.15 A). W ith increasing Sr²⁺ concentration, the bandwidth increases. W ith changes in x, intriguing spin, charge, and orbital phases are produced and extensive studies have been perform ed on these system s.¹

In the x = 0.5 compound, on cooling from room tem perature, a transition from a param agnetic insulating (PM I) phase to a ferrom agnetic m etallic (FMM) phase occurs at 255 K and a transition from FMM phase to charge-ordered (CO) antiferrom agnetic insulating (AFI) phase is observed at 155 K. The magnetic structure in the CO AFI phase is CE-type.² W ith the application of a magnetic eld, the FMM state is enhanced and the charge-ordering state is suppressed completely above 7 T.³ The magnetic eld induced collapse of CO state is accompanied by a structural transition in which the volum e increases drastically, leading to large positive magnetovolume e ect. Orbital ordering coincides with charge-ordering. Di erent orbital ordering types, d_{3x^2} $r^2 = d_{3y^2}$ r^2 -type⁵ or d_{x^2} v^2 -type⁶ have been suggested in this compound.

 $N d_{0:45} Sr_{0:55} M nO_3$ is an A-type antiferrom agnetic m etalwith coupled m agnetic and structural transition at

225 K $\stackrel{?}{\cdot}$ T he M n m om ents are ferrom agnetically aligned in the ab-plane in Pbnm symmetry. Charge carriers are conned within the ab-plane while the transport along the c-axis is quenched, leading to highly anisotropic resistivity ($_{\rm c}=_{\rm ab}$ 10⁴ at 35 m K).⁷ The antiferrom agnetic spin ordering is accompanied by the $d_{\rm x^2}$ $_{\rm y^2}$ -type orbital ordering, both of which are simultaneously destroyed by high magnetic elds, concomitant with a discontinuous decrease of resistivity.⁸

In this manganite system, the magnetic, electronic and orbital transitions are correlated with an abrupt structural transition, in which the a and b lattice pa-

ram eters are elongated and the c parameter is com pressed (in P bnm symmetry).⁷ O ther groups showed that in Nd_{0:5}Sr_{0:5}MnO₃, during the transition from FMM to AFICO state, the crystal symmetry is lowered to m onoclinic P 21/m .9,10 R itter et al.11 suggested that the low tem perature AFICO phase is phase-segregated into two di erent crystallographic structures and three m agnetic phases: orthorhom bic (Imma) ferrom agnetic, orthorhom bic (Im m a) A -type antiferrom agnetic, and m onoclinic (P21/m) charge-ordered CE-type antiferrom agnetic phases, in which a magnetic eld can induce the charge-ordered m onoclinic phase to collapse and to transform into the FMM orthorhom bic phase. Kajim oto et al¹² showed that in the CE-type and A-type antiferrom agnetic states, the M nO 6 octahedra are apically com pressed corresponding to d_{3x^2} $r^2 = d_{3y^2}$ r^2 or d_{x^2} y^2 orbital ordering.

Hydrostatic and uniaxial pressures a ect the CO and FMM states di erently. In Nd_{0:5}Sr_{0:5}M nO₃, hydrostatic pressure (< 1 GPa) increases T_c with dT_c/dP = 6.8 K/GPa and decreases T_{c0} at a rate of 8.4 K/GPa,¹³ while uniaxial pressure along the c-axis decreases T_c at a rate of 60 K/GPa and increases T_{c0} at a rate of 190 K/GPa.¹⁴ In Nd_{0:45}Sr_{0:55}M nO₃, with the application of uniaxial pressure along the c-axis, the A-type antiferrom agnetic phase is stabilized by increasing T_N at 66 K/GPa, in plying the stabilization of the d_{x² y²} orbital.¹⁴ In thin Im s, due to the e ect of substrate, biaxial strain can be induced. In Nd_{0:5}Sr_{0:5}M nO₃ thin

In s, the thickness dependent strain tunes the competition between CO insulating and FMM states,¹⁵ and there are optimal strain conditions under which the CO or m etallic states appear.¹⁶

The correlation between the structure and the electronic and magnetic transitions indicates its crucial role in this doping system. We have studied the CO, FMM, and antiferrom agnetic state changes in $Nd_{0:55}Sr_{0:45}MnO_3$ and $Nd_{0:5}Sr_{0:5}MnO_3$ through high-pressure (up to 6 GPa) resistivity and structure mea-



FIG. 1: Resistivity of (a) $N\,d_{0:55}\,S\,r_{0:45}\,M\,nO_3$ and (b) $N\,d_{0:55}\,S\,r_{0:5}\,M\,nO_3$ under pressure.

surements. It is found that pressure induces similar electronic and m agnetic behavior in them, which can be partially related to the changes of orthorhom bic distortion under pressure.

II. SAM PLES AND EXPERIMENTAL METHODS

The samples were prepared by solid-state reaction. Stoichiom etric amounts of Nd_2O_3 , MnO_2 , and $SrCO_3$ pow derwerem ixed, ground, and calcined at 900 $^\circ\!\mathrm{C}$ for 15 hours. The sample was then cooled down to room tem perature and reground and then calcined again at 1200 $^\circ\!\mathrm{C}$ for 17 hours. The powder was then pressed into pellets. The pellets were sintered at 1500 °C for 12 hours, cooled down to 800 °C at a rate of 5 °C/m in, and then quickly cooled down to room temperature. The pellets were annealed at 1200 $^{\circ}\mathrm{C}$ and cooled down slow ly to room tem perature at 1 $^{\circ}C/m$ in. The x-ray powder di raction patterns show a single crystallographic phase for each sam ple. The magnetization and resistivity measurements are consistent with the results of other groups.^{1,17,18} The details of the high-pressure resistivity and high-pressure x-ray di raction m easurem ent m ethods and error analysis were described previously.19

III. RESULTS AND DISCUSSIONS

A. Nd_{0:55}Sr_{0:45}M nO₃

 $N d_{0:55} Sr_{0:45} M nO_3$ is a double exchange compound, with a FMM to PM I transition at 280 K upon warm -



FIG.2: Transition tem peratures of (a) N d_{0:55} Sr_{0:45} M nO $_3$ and (b) N d_{0:55} Sr_{0:5} M nO $_3$. The solid lines are third-order polynomial ts as guides to the eyes. (a) M etal-insulator transition tem perature of N d_{0:55} Sr_{0:45} M nO $_3$ where the inset shows the resistivity changes with pressure in PM I phase [at 316 K (solid circle)] and FM M phase [at 120 K (open circle)]; (b) M etal-insulator transition (solid circle) and charge-ordering transition (solid square) tem peratures of N d_{0:5} Sr_{0:5} M nO $_3$.

ing. Under pressure, the electron transport is modied in an interesting manner. Figure 1(a) shows the resistivity as a function of temperature and pressure. The most important feature is the insulating state arising at low temperature under pressure. With pressure increase, the insulating behavior dom inates above 6 GPa. Consequently, the resistivity in the measured tem perature range changes with pressure [inset of Fig. 2(a)]. Below 3.5 GPa, the resistivity in the PM I phase is reduced while in the FMM phase it is almost unchanged. Above 3.5 GPa, in both phases, resistivity increases rapidly with pressure. In the low -pressure range, the metal-insulator transition temperature $T_{M I}$ increases with pressure. Due to the limit of the instrument, T $_{\rm M~I}$ above 325 K in the range of 2-4 GPa cannot be determ ined. Above 4 GPa, the transition temperature decreases on pressure increase. Above 6 GPa, the insulating behavior dom inates so that the transition tem perature cannot be determ ined, although there is still a trace of m etallic behavior. The change of transition tem perature with pressure is plotted in Fig. 2 (a). The third-order polynomial tgives a critical pressure P* 2.6 GPa, while the resistivity in param agnetic phase (at 316 K) gives

P* 3.6 GPa [inset of Fig. 2(a)].

In this com pound, the behavior of $T_{M I}$ and resistivity is similar to that found in La_{0:60}Y_{0:07}Ca_{0:33}M nO₃ (R ef. 19) and Pr_{0:7}Ca_{0:3}M nO₃²⁰ However, the mechanism by which the materials become insulating at high-pressures is di erent. In those two compounds, the materials becom e insulating through the suppression of the FM M state, displaying a decreasing $T_{M\ I}$ above critical pressure. In N d_{0:55}Sr_{0:45}M nO₃, the insulating state at high pressures has two origins: the suppression of the FM M state and the expansion of a low tem perature insulating phase, which appears with pressure increase and nally dom inates at high pressures. The enhancement of the insulating phase is the dom inant contribution to the change in resistivity.

A bram ovich et al.²¹ proposed a phase-separation m odel in which the AFI droplets lie in a conducting ferrom agnetic host. In the phase-separation m odel, the behavior of the m aterial becom ing insulating can be understood as pressure induced percolation where the increasing pressure suppresses the FMM component and enhances AFI component above P*.

It is noted that the transport behavior at high pressures where the compound becomes insulating is similar to that of $Nd_{0:45}Sr_{0:55}MnO_3$ at ambient pressure.²² W hen high magnetic eld of 35 T is applied, the resistivity of the A-type antiferrom agnetic m etallic $Nd_{0:45}Sr_{0:55}MnO_3$ becomes similar to that of $Nd_{0:55}Sr_{0:45}Sn_{0:55}MnO_3$, which is ascribed to the destruction of the A-type antiferrom agnetic spin ordering and $d_{x^2 y^2}$ orbital ordering.⁸ C onsidering the similarity between the resistivity of x = 0.45 com pound under high-pressure and x = 0.55 at ambient pressure²² and that of x = 0.55 in high magnetic eld,⁸ one might speculate that the state induced by pressure in x = 0.45 com pound has a similar spin and orbital structure to $Nd_{0:45}Sr_{0:55}MnO_3$.

W ith the high-pressure structural measurements, it is found that the lattice is compressed anisotropically by pressure. The varying rates of change of lattice parameters under pressure lead to further distortion of the unit cell. To describe the orthorhom bic distortion, M energhini et al.²³ de ned the ab-plane distortion (O s_{ab} = $2\frac{a}{a+b}$) and c-axis distortion (O c = $2\frac{a+b}{a+b+c}\frac{p}{2}$) (in Pbnm sym - metry). When the lattice is cubic, both O s_{ab} and O c are zero. Figure 3 (a) show sthat both distortions increase under pressure, indicating a more distorted structure from the cubic case.

The structure of $Nd_{0:45}Sr_{0:55}MnO_3$ is O^z (a b < $\frac{p^2}{2}$).¹² The corresponding orthorhom bic distortion is 0 in the ab-plane and -2% along the c-axis (calculated with the data in Ref. 12), which corresponds to the d_{x^2} v^2 -type orbital ordering and the A-type antiferrom agnetic m etal state. Under pressure, the orthorhom bic distortion for both the c-axis and the ab-plane increase in Nd_{0:55}Sr_{0:45}M nO₃, indicating that the high-pressure structure is more di erent from Nd_{0:45}Sr_{0:55}M nO₃ than at am bient pressure. The ab-plane distortion increase of N d_{0:55} Sr_{0:45}M nO _3 under pressure in plies that the orbital state is di erent from that of Nd_{0.45}Sr_{0.55}M nO₃ at am bient pressure. However, the sim ilarity between the resistivities (in both absolute value and shape) seems to suggest that pressure induces an A-type antiferrom aqnetic state in $Nd_{0:55}Sr_{0:45}M$ nO₃.



FIG. 3: Pressure dependence of the ab-plane and c-axis orthorhom bic distortions of (a) $N d_{0.55} Sr_{0.45} M nO_3$ and (b) $N d_{0.55} Sr_{0.5} M nO_3$. (The dashed lines are guides to the eye.)

B. Nd_{0:5}Sr_{0:5}M nO₃

Figure 1 (b) shows the resistivity of N d_{0:5}Sr_{0:5}M nO₃ under pressure. In the low tem perature CO AFI phase, the resistivity is reduced by pressure. On the other hand, the insulating region extends to higher temperature so that the ferrom agnetic m etallic state is suppressed. If the tem perature where insulating and metallic states cross (the resistivity minimum) is de ned as CO transition tem perature, T_{CO} increases rst with pressure and appears to decrease above 3.8 GPa [Fig. 2(b)]. At the same time, pressure a ects the metal-insulator transition only slightly. W ith pressure increase, $T_{M I}$ increases 3 GPa and drops above 3 GPa. The highest below $T_{M,T}$ is only 4 K higher than that at am bient pressure. In the measured pressure range, resistivity in the PM I phase is suppressed.

 $T_{\rm C\,O}$ increases with pressure below $3.8~{\rm GPa}$ while $T_{\rm M~I}$ shows alm ost no change [Fig. 2(b)]. This is di erent from the result that hydrostatic pressure (<1 GPa) increases $T_{\rm C}$ and decreases $T_{\rm C\,O}$ reported by other authors in single crystals. 13 On the contrary, our results are consistent with the e ects of uniaxial pressure along the c-axis. 14 In Fig. 3(b), it is seen that the c-axis distortion increases while the ab-plane distortion decreases with pressure. Because the CO state corresponds to a higher orthorhom bic distortion state, 3 possibly the pressure induced increase of c-axis distortion enhances the CO state. On the other hand, the decrease in the ab-plane distortion may enhance the electron hoping and

lead to the resistivity decrease in the ab-plane.

Roy et al.²⁴ reported that pressure above 1.5 GPa splits the coincident antiferrom agnetic and chargeordering transitions in which $T_{\,C\,O}\,$ increases while $T_{\,N}\,$ decreases. With the transitions decoupled, resistivity rises abruptly at the magnetic transition but not at the CO transition, in plying that low tem perature resistivity com es m ostly from the CE-type antiferrom agnetic state. W e did not observe the T_{CO} and T_N splitting in a larger pressure range, possibility because our sample is polycrystalline. In this case, the grain size distribution and random ly distributed grain orientations may lead to the broader CO AFI transition in polycrystalline sam ples¹⁷ than in single crystal.³ However, the large suppression of resistivity indicates that the antiferrom agnetic state, speci cally the CE-type antiferrom agnetic state, is suppressed, which is also consistent with the ab-plane orthorhom bic distortion reduction [Fig. 3(b)].

In $Nd_{0:5}Sr_{0:5}M$ nO₃, by substituting Nd^{3+} with larger size La³⁺, the bandwidth is increased and hence the CO phase is suppressed and T_C increases. With applied pressure, a transition from the CO CE-type AFI to the A-type AFI was suggested, in which resistivity is suppressed and T $_{\rm C\,O}\,$ gradually increases with pressure. 25 This is consistent with our result in the parent com pound $Nd_{0:5}Sr_{0:5}M nO_3$ and at a much higher pressure. The smaller ab-plane distortion and larger c-axis distortion at high pressures may favor an A-type antiferrom agnetic state and $d_{x^2 \ v^2}$ orbital ordering as in the x = 0.55 compound. In the A-type AFI state, resistivity is decreased due to enhanced in-plane transfer integral by the reduction of in-plane distortion. In the phase-separation m odel,¹¹ the A-type antiferrom agnetic phase is enhanced and the CO CE -type antiferrom agnetic phase is suppressed concom itantly by pressure. Because the bandwidth is sensitive to the atom ic structure of the M nO₆ octahedra, especially the M n-O-M n bond angle, it is highly desired to measure the atom ic structure to explain the electronic and m agnetic behavior under pressure. Unfortunately, it has been found di cult to acquire the atom ic structure inform ation from x-ray di raction, due to the large di erence between the scattering factors of the Nd/Sr and oxygen atom s compared to the case of La_{0:6}Y_{0:07}Ca_{0:33}M nO₃ in our previous work,¹⁹ which makes the renement to the oxygen coordinates in the unit cellextrem ely di cult. A similar case also exists in the study on the structure of PbO under high-pressure.²⁶ So other experim ental techniques, such as high-pressure R am an scattering, are proposed to probe the local structure changes under pressure.

The two Nd₁ $_{x}$ Sr_xM nO₃ m anganites at x = 0.45 and 0.5 have very di erent electronic, m agnetic, and orbital ground states at am bient conditions. However, when we compare the resistivity at high-pressure, we can nd a surprising similarity between them [Figs.1(a) and 1(b)]. Figure 4 is an example of the resistivity of these two compounds at pressures above the critical pressure. The similarity also seem s to imply a similar electronic and



240

280

320

FIG. 4: Comparison of resistivity of N d_{0:55}Sr_{0:45}M nO₃ and N d_{0:5}Sr_{0:5}M nO₃ under pressure. The inset shows the resistivity of N d_{0:5}Sr_{0:5}M nO₃ thin ln s with di erent thicknesses from R ef. 15 for comparison with our pressure results.

160

200

T (K)

6

5

4

3

80

120

ρ (10⁻³ Ω cm)

m agnetic state. The structuralm easurements partly justify this assumption. The orthorhom bic distortion of x = 0.45 is increased by pressure to almost the same as that of the x = 0.5 compound at ambient pressure [Figs. 3 (a) and 3 (b)]. In addition, the similarity between the high-pressure resistivity of these two compounds and that of N d_{0:45} Sr_{0:55}M nO₃ also suggests an A-type AFI phase in the high-pressure phase.

It is interesting to compare the e ects of pressure and strain in thin $\,$ lm s. The inset of F ig. 4 shows the resistivity of N d_{0:5} Sr_{0:5} M nO_3 thin $\,$ lm s of several typical thicknesses from P rellier et al. 15 W ith thickness decrease, the strain in thin $\,$ lm s is found to increase. 16 C om pared with N d_{0:55} Sr_{0:45} M nO_3, the resistivity evolution with thickness decrease (strain increase) is in analogy to pressure increase in bulk N d_{0:55} Sr_{0:45} M nO_3, indicating that pressure increases strain in bulk sample proved by structure m easurem ents.

IV. SUMMARY

In sum m ary, by studying the resistivity and structure of N d₁ $_x$ Sr_xM nO₃ (x = 0.45, 0.5) at high pressures, it is found that they have a sim ilar resistivity as a function of temperature, which results from the di erent e ects of pressure on their structures. Under pressure, both the ferrom agnetic m etallic state in the x = 0.45 com pound and the CE -type antiferrom agnetic insulating state in the x = 0.5 com pound are suppressed. By com paring the resistivity and structure with the x = 0.55 com pound, pressure appears to induce a sim ilar electronic and m agnetic state in these two com pounds with m uch di erent ground states. W e suggest that the pressure induced m agnetic states in both sam ples are A-type antiferrom agnetic.

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- ¹ Y.Tokura and Y.Tom ioka, J.M agn.M agn.M ater. 200, 1 (1999).
- ² H. Kawano, R. Kajim oto, H. Yoshizawa, Y. Tom ioka, H. Kuwahara, and Y. Tokura, Phys. Rev. Lett. 78,, 4253 (1997).
- ³ H. Kuwahara, Y. Tomioka, A. Asamitsu, Y. Moritomo, and Y. Tokura, Science 270, 961 (1995).
- ⁴ R.Mahendiran, M.R.Ibarra, A.Maignan, F.Millange, A.Arulraj, R.Mahesh, B.Raveau, and C.N.R.Rao, Phys.Rev.Lett. 82, 2191 (1999).
- ⁵ K. Nakam ura, T. Arim a, A. Nakazawa, Y. Wakabayashi, and Y. Murakami, Phys. Rev. B 60, 2425 (1999).
- ⁶ S.Zvyagin, A.Angerhofer, K.V.Kamenev, L.C.Brunel, G.Balakrishnan, and D.M.Paul, Solid State Commun. 121, 117 (2002).
- ⁷ H. Kuwahara, T. Okuda, Y. Tomioka, T. Kimura, A.Asamitsu, and Y. Tokura, Mat. Res. Soc. Sym p. Proc. 494, 83 (1998).
- ⁸ T.Hayashi, N.Miura, K.Noda, H.Kuwahara, S.O kam oto, S. Ishihara, and S.Maekawa, Phys. Rev. B 65, 024408 (2002).
- ⁹ V. Eremenko, S. Gnatchenko, N. Makedonska, Y. Shabakayeva, M. Shvedun, V. Sirenko, J. Fink-Finowicki, K.V. Kamenev, G. Balakrishnan, and D. M. Paul, Low Temp. Phys. 27, 930 (2001).
- ¹⁰ P. La ez, G. V. Tendebo, F. M illange, V. Caignaert, M. Hervieu, and B. Raveau, Mater. Res. Bull. 31, 905 (1996).
- ¹¹ C. Ritter, R. Mahendiran, M. R. Ibarra, L. Morellon, A. Maignan, B. Raveau, and C. N. R. Rao, Phys. Rev. B 61, R9229 (2000).
- $^{\rm 12}\,$ R . K a jim oto, H . Yoshizawa, H . K awano, H . K uwahara,

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- Y. Tokura, K. Ohoyama, and M. Ohashi, Phys. Rev. B 60, 9506 (1999).
- ¹³ Y.M oritom o, H.K uwahara, and Y.Tokura, J.Phys.Soc. Jpn. 66, 556 (1997).
- ¹⁴ T.hisa A rim a and K.N akam ura, Phys. Rev. B 60, R 15013 (1999).
- ¹⁵ W . Prellier, A. B iswas, M. Rajeswari, T. Venkatesan, and R. L. Greene, Appl. Phys. Lett. 75, 397 (1999).
- ¹⁶ Q. Qian, T. A. Tyson, C.-C. Kao, W. Prellier, J. Bai, A. Biswas, and R. L. Greene, Phys. Rev. B 63, 224424 (2001).
- ¹⁷ V. Caignaert, F. M illange, M. Hervieu, E. Suard, and B.Raveau, Solid State Commun. 99, 173 (1996).
- ¹⁸ Y. Tom ioka, H. Kuwahara, A. Asam itsu, M. Kasai, and Y. Tokura, Appl. Phys. Lett. 70, 3609 (1997).
- ¹⁹ C.Cui, T.A.Tyson, Z.Zhong, J.P.Carb, and Y.Qin, Phys.Rev.B 67, 104107 (2003).
- ²⁰ C.Cuiand T.A.Tyson, Appl.Phys.Lett.83, 2856 (2003).
- ²¹ A. I. A bram ovich, A. V. Michurin, O. Y. Gorbenko, and A. R. Kaul, J. Phys.: Condens. Matter 12, L627 (2000).
- ²² H.Kuwahara, T.Okuda, Y.Tomioka, A.Asamitsu, and Y.Tokura, Phys. Rev. Lett. 82, 4316 (1999).
- ²³ C.M eneghini, D.Levy, S.M obilio, M.O rtolani, M.Nunez-Reguero, A.Kum ar, and D.D.Sarm a, Phys.Rev.B 65, 012111 (2002).
- ²⁴ A.S.Roy, A.Husmann, T.F.Rosenbaum, and J.F. Mitchell, Phys.Rev.B 63, 094416 (2001).
- ²⁵ Y. Moritomo, H. Kuwahara, Y. Tomika, and Y. Tokura, Phys. Rev. B 55, 7549 (1997).
- ²⁶ U.Haussenm ann, P.Berastegui, S.Carlson, J.Haines, and J.M. Leger, Angew. Chem. Int. Ed. 40, 4624 (2001).